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List of Publications by Citations

192 papers	1,284 citations	19 h-index	27 g-index
209 ext. papers	1,501 ext. citations	1.2 avg, IF	3.95 L-index

#	Paper	IF	Citations
192	High performance quantum dot lasers on GaAs substrates operating in 1.5 [micro sign]m range. *Electronics Letters*, **2003**, 39, 1126	1.1	126
191	Highly efficient injection microdisk lasers based on quantum well-dots. *Optics Letters*, **2018**, 43, 4554-4557	3	39
190	InAs/InGaAsN quantum dots emitting at 1.55 μm grown by molecular beam epitaxy. *Journal of Crystal Growth*, **2003**, 251, 388-391	1.6	37
189	A 1.33 μm InAs/GaAs quantum dot laser with a 46 cm−1 modal gain. *Semiconductor Science and Technology*, **2008**, 23, 105004	1.8	36
188	Ultrasmall microdisk and microring lasers based on InAs/InGaAs/GaAs quantum dots. *Nanoscale Research Letters*, **2014**, 9, 3266	5	34
187	Heat-sink free CW operation of injection microdisk lasers grown on Si substrate with emission wavelength beyond 1.3 μm. *Optics Letters*, **2017**, 42, 3319-3322	3	33
186	Metamorphic growth for application in long-wavelength (1.3–1.55 μm) lasers and MODFET-type structures on GaAs substrates. *Nanotechnology*, **2004**, 15, S283-S287	3.4	32
185	Continuous-wave lasing at 100 °C in 1.3 μm quantum dot microdisk diode laser. *Electronics Letters*, **2015**, 51, 1354-1355	1.1	29
184	Light Outcoupling from Quantum Dot-Based Microdisk Laser via Plasmonic Nanoantenna. *ACS Photonics*, **2017**, 4, 275-281	6.3	27
183	Single quantum well deep-green LEDs with buried InGaN/GaN short-period superlattice. *Journal of Crystal Growth*, **2011**, 315, 267-271	1.6	27
182	Metamorphic 1.5 μm-range quantum dot lasers on a GaAs substrate. *Semiconductor Science and Technology*, **2006**, 21, 691-696	1.8	26
181	Whispering-gallery mode microcavity quantum-dot lasers. *Quantum Electronics*, **2014**, 44, 189-200	1.8	24
180	Degradation-robust single mode continuous wave operation of 1.46 μm metamorphic quantum dot lasers on GaAs substrate. *Applied Physics Letters*, **2006**, 89, 041113	3.4	24
179	Metamorphic lasers for 1.3-μm spectral range grown on GaAs substrates by MBE. *Semiconductors*, **2003**, 37, 1119-1122	0.7	24
178	Room Temperature Lasing in 1-μm Microdisk Quantum Dot Lasers. *IEEE Journal of Selected Topics in Quantum Electronics*, **2015**, 21, 709-713	3.8	22
177	Improvement of temperature-stability in a quantum well laser with asymmetric barrier layers. *Applied Physics Letters*, **2012**, 100, 021107	3.4	22
176	High-power 1.5 μm InAs-InGaAs quantum dot lasers on GaAs substrates. *Semiconductors*, **2004**, 38, 732-735	0.7	22

175	Light Emitting Devices Based on Quantum Well-Dots. *Applied Sciences (Switzerland)*, **2020**, 10, 1038	2.6	20
174	The influence of heat treatment conditions on the evaporation of defect regions in structures with InGaAs quantum dots in the GaAs matrix. *Semiconductors*, **2002**, 36, 1020-1026	0.7	20
173	Growth and Characterization of GaP/GaPAs Nanowire Heterostructures with Controllable Composition. *Physica Status Solidi - Rapid Research Letters*, **2019**, 13, 1900350	2.5	19
172	Bandedge-engineered quantum well laser. *Semiconductor Science and Technology*, **2011**, 26, 055025	1.8	18
171	Direct modulation characteristics of microdisk lasers with InGaAs/GaAs quantum well-dots. *Photonics Research*, **2019**, 7, 664	6	16
170	Control of emission spectra in quantum dot microdisk/microring lasers. *Optics Express*, **2014**, 22, 25782-7	3.3	14
169	High speed data transmission using directly modulated microdisk lasers based on InGaAs/GaAs quantum well-dots. *Optics Letters*, **2019**, 44, 5442-5445	3	14
168	Mode selection in InAs quantum dot microdisk lasers using focused ion beam technique. *Optics Letters*, **2015**, 40, 4022-5	3	13
167	Elevated temperature lasing from injection microdisk lasers on silicon. *Laser Physics Letters*, **2018**, 15, 015802	1.5	13
166	Enhanced light outcoupling in microdisk lasers via Si spherical nanoantennas. *Journal of Applied Physics*, **2018**, 124, 163102	2.5	13
165	Electrically pumped InGaAs/GaAs quantum well microdisk lasers directly grown on Si(100) with Ge/GaAs buffer. *Optics Express*, **2017**, 25, 16754-16760	3.3	12
164	A monolithic white LED with an active region based on InGaN QWs separated by short-period InGaN/GaN superlattices. *Semiconductors*, **2010**, 44, 808-811	0.7	12
163	Microdisk Injection Lasers for the 1.27-Êm Spectral Range. *Semiconductors*, **2016**, 50, 390-393	0.7	12
162	Evaluation of energy-to-data ratio of quantum-dot microdisk lasers under direct modulation. *Journal of Applied Physics*, **2019**, 126, 063107	2.5	10
161	Observation of zero linewidth enhancement factor at excited state band in quantum dot laser. *Electronics Letters*, **2015**, 51, 1686-1688	1.1	10
160	Modeling, synthesis and study of highly efficient solar cells based on III-nitride nanowire arrays grown on Si substrates. *Journal of Physics: Conference Series*, **2015**, 643, 012115	0.3	10
159	Light-current characteristic of a quantum well laser with asymmetric barrier layers. *Journal of Applied Physics*, **2013**, 114, 143103	2.5	10
158	Semiconductor lasers with asymmetric barrier layers: An approach to high temperature stability. *Semiconductors*, **2011**, 45, 530-535	0.7	10

157	Nanofaceting and alloy decomposition: From basic studies to advanced photonic devices. *Microelectronics Journal*, **2006**, 37, 1451-1460	1.8	10
156	Optical and structural properties of InAs quantum dot arrays grown in an InxGa1− As matrix on a GaAs substrate. *Semiconductors*, **2004**, 38, 833-836	0.7	10
155	Nonequilibrium room-temperature carrier distribution in InAs quantum dots overgrown with thin AlAs/InAlAs layers. *Semiconductors*, **2005**, 39, 1188	0.7	10
154	Continuous-wave lasing of single-mode metamorphic quantum dot lasers for the 1.5-μm spectral region. *Semiconductors*, **2005**, 39, 1415	0.7	10
153	Suppression of sublinearity of light–current curve in 850-nm quantum well laser with asymmetric barrier layers. *Electronics Letters*, **2015**, 51, 1106-1108	1.1	9
152	Coherent Growth of InP/InAsP/InP Nanowires on a Si (111) Surface by Molecular-Beam Epitaxy. *Technical Physics Letters*, **2018**, 44, 112-114	0.7	9
151	High-temperature lasing in a microring laser with an active region based on InAs/InGaAs quantum dots. *Semiconductors*, **2012**, 46, 1040-1043	0.7	9
150	Properties of InGaAsN heterostructures emitting at 1.3–1.55 μm. *Semiconductor Science and Technology*, **2005**, 20, 961-965	1.8	9
149	InAs/GaAs Quantum Dot Microlasers Formed on Silicon Using Monolithic and Hybrid Integration Methods. *Materials*, **2020**, 13,	3.5	9
148	Single-Mode Emission From 4-μm Microdisk Lasers With Dense Array of InGaAs Quantum Dots. *Journal of Lightwave Technology*, **2015**, 33, 171-175	4	8
147	Electroluminescence of GaP x N y As1 − x − y nanoheterostructures through a transparent electrode made of CVD graphene. *Semiconductors*, **2012**, 46, 796-800	0.7	8
146	Optical properties of quantum-confined heterostructures based on GaP x N y As1 − x − y alloys. *Semiconductors*, **2011**, 45, 1164-1168	0.7	8
145	Stresses in selectively oxidized GaAs/(AlGa)xOy structures. *Semiconductors*, **2005**, 39, 748-753	0.7	8
144	Impact of Self-Heating and Elevated Temperature on Performance of Quantum Dot Microdisk Lasers. *IEEE Journal of Quantum Electronics*, **2020**, 56, 1-8	2	8
143	Thermal resistance of ultra-small-diameter disk microlasers. *Semiconductors*, **2015**, 49, 674-678	0.7	7
142	Room-temperature lasing in microring cavities with an InAs/InGaAs quantum-dot active region. *Semiconductors*, **2013**, 47, 1387-1390	0.7	7
141	On the optimization of asymmetric barrier layers in InAlGaAs/AlGaAs laser heterostructures on GaAs substrates. *Semiconductors*, **2015**, 49, 935-938	0.7	7
140	Lasing in microdisks of ultrasmall diameter. *Semiconductors*, **2014**, 48, 1626-1630	0.7	7

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138	Longitudinal photonic bandgap crystal laser diodes with ultra-narrow vertical beam divergence **2006**,		7
137	Quantum-dot microlasers based on whispering gallery mode resonators. *Light: Science and Applications*, **2021**, 10, 80	16.7	7
136	Multilayer heterostructures for quantum-cascade lasers operating in the terahertz frequency range. *Semiconductors*, **2016**, 50, 662-666	0.7	7
135	Theory of the power characteristics of quantum-well lasers with asymmetric barrier layers: Inclusion of asymmetry in electron- and hole-state filling. *Semiconductors*, **2016**, 50, 1362-1368	0.7	7
134	The effect of asymmetric barrier layers in the waveguide region on power characteristics of QW lasers. *Technical Physics Letters*, **2015**, 41, 439-442	0.7	6
133	Effect of asymmetric barrier layers in the waveguide region on the temperature characteristics of quantum-well lasers. *Semiconductors*, **2012**, 46, 1027-1031	0.7	6
132	Optical and structural properties of InGaN/GaN short-period superlattices for the active region of light- emitting diodes. *Semiconductors*, **2010**, 44, 828-834	0.7	6
131	Molecular beam epitaxy growth methods of wavelength control for InAs/(In)GaAsN/GaAs heterostructures. *Nanotechnology*, **2008**, 19, 445715	3.4	6
130	Methods of controlling the emission wavelength in InAs/GaAsN/InGaAsN heterostructures on GaAs substrates. *Semiconductors*, **2008**, 42, 805-812	0.7	6
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126	Record Low Threshold Current Density in Quantum Dot Microdisk Laser. *Semiconductors*, **2019**, 53, 1888–1890	0.7	6
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124	3.5-μm radius race-track microlasers operating at room temperature with 1.3-μm quantum dot active region. *Journal of Applied Physics*, **2017**, 121, 043104	2.5	5
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122	Optical properties of quaternary GaN x As y P1 − x − y semiconductor alloys. *Semiconductors*, **2010**, 44, 857-860	0.7	5

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119	Structural and optical characterization of dilute phosphide planar heterostructures with high nitrogen content on silicon. *CrystEngComm*, **2020**, 22, 283-292	3.3	5
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117	Dynamics of Broadband Lasing Cascade from a Single Dot-in-well InGaAs Microdisk. *Scientific Reports*, **2019**, 9, 5635	4.9	4
116	Optical and electrical properties of silicon nanopillars. *Semiconductors*, **2015**, 49, 939-943	0.7	4
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113	Laser generation in microdisc resonators with InAs/GaAs quantum dots transferred on a silicon substrate. *Technical Physics Letters*, **2013**, 39, 830-833	0.7	4
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111	Broad-area InAs□GaAs quantum dot lasers incorporating Intermixed passive waveguide. *Electronics Letters*, **2007**, 43, 29	1.1	4
110	Optical studies of asymmetric-waveguide submonolayer InGaAs QD microdisks formed by selective oxidation. *Semiconductors*, **2006**, 40, 476-480	0.7	4
109	Lasing wavelength of quantum dot heterostructures controlled within the 1.3□0.85 □m range by means of high-temperature annealing. *Technical Physics Letters*, **2004**, 30, 644-646	0.7	4
108	Effect of carrier localization on the optical properties of MBE-grown GaAsN/GaAs heterostructures. *Semiconductors*, **2002**, 36, 997-1000	0.7	4
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104	Resonance reflection of light by ordered silicon nanopillar arrays with the vertical p-n junction. *Thin Solid Films*, **2019**, 672, 109-113	2.2	4

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102	On the high characteristic temperature of an InAs/GaAs/InGaAsP QD laser with an emission wavelength of ~1.5 μm on an InP substrate. *Semiconductors*, **2017**, 51, 1332-1336	0.7	3
101	Energy Consumption for High-Frequency Switching of a Quantum-Dot Microdisk Laser. *Technical Physics Letters*, **2019**, 45, 847-849	0.7	3
100	The effect of sulfide passivation on luminescence from microdisks with quantum wells and quantum dots. *Technical Physics Letters*, **2015**, 41, 654-657	0.7	3
99	Laser generation at 1.3 μm in vertical microcavities containing InAs/InGaAs quantum dot arrays under optical pumping. *Technical Physics Letters*, **2016**, 42, 1009-1012	0.7	3
98	Lasing in microdisk resonators with InAs/InGaAs quantum dots transferred on a silicon substrate. *Journal of Physics: Conference Series*, **2014**, 541, 012049	0.3	3
97	Effect of the nonlinear saturation of the gain on the peak modulation frequency in lasers based on self-assembled quantum dots. *Semiconductors*, **2011**, 45, 966-970	0.7	3
96	Structural and optical properties of InAlN/GaN distributed Bragg reflectors. *Semiconductors*, **2010**, 44, 949-953	0.7	3
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92	Violation of Local Electroneutrality in the Quantum Well of a Semiconductor Laser with Asymmetric Barrier Layers. *Semiconductors*, **2018**, 52, 1621-1629	0.7	3
91	Specific features of waveguide recombination in laser structures with asymmetric barrier layers. *Semiconductors*, **2017**, 51, 254-259	0.7	2
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89	Lasing of metamorphic hybrid 1300nm spectral band VCSEL under optical pumping up to 120 °C **2017**,		2
88	Comparative Analysis of Injection Microdisk Lasers Based on InGaAsN Quantum Wells and InAs/InGaAs Quantum Dots. *Semiconductors*, **2020**, 54, 263-267	0.7	2
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86	Improved emission outcoupling from microdisk laser by Si nanospheres. *Journal of Physics: Conference Series*, **2016**, 741, 012158	0.3	2

85	Optical properties of metamorphic hybrid heterostuctures for vertical-cavity surface-emitting lasers operating in the 1300-nm spectral range. *Semiconductors*, **2017**, 51, 1127-1132	0.7	2
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83	Formation of composite InGaN/GaN/InAlN quantum dots. *Semiconductors*, **2010**, 44, 1338-1341	0.7	2
82	High-gain injection quantum-dot lasers operating at wavelengths above 1300 nm. *Technical Physics Letters*, **2008**, 34, 1008-1010	0.7	2
81	Lasing properties of strain-compensated InAs/InGaAsN/GaAsN heterostructures in 1.3–1.55 μm spectral range. *Technical Physics Letters*, **2006**, 32, 229-231	0.7	2
80	Room-temperature 1.3-μm lasing in a microdisk with quantum dots. *Semiconductors*, **2006**, 40, 1101-1104	0.7	2
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75	Strip-loaded horizontal slot waveguide for routing microdisk laser emission. *Journal of the Optical Society of America B: Optical Physics*, **2020**, 37, 1878	1.7	2
74	MBE growth, structural and optical properties of multilayer heterostructures for quantum-cascade lasers. *Journal of Physics: Conference Series*, **2017**, 917, 052012	0.3	2
73	Synthesis of Morphologically Developed InGaN Nanostructures on Silicon: Influence of the Substrate Temperature on the Morphological and Optical Properties. *Semiconductors*, **2020**, 54, 1075-1077	0.7	2
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71	The Use of Microdisk Lasers Based on InAs/InGaAs Quantum Dots in Biodetection. *Technical Physics Letters*, **2019**, 45, 1178-1181	0.7	2
70	Study of p-type contact topography influence on characteristics of microdisk and microring lasers. *Journal of Physics: Conference Series*, **2018**, 1124, 041012	0.3	2
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68	Phosphorus-Based Nanowires Grown by Molecular-Beam Epitaxy on Silicon. *Semiconductors*, **2018**, 52, 1416-1419	0.7	2

67	Reflection Spectra of Microarrays of Silicon Nanopillars. *Optics and Spectroscopy (English Translation of Optika I Spektroskopiya)*, **2018**, 124, 730-734	0.7	2
66	1.3 μm optically-pumped monolithic VCSEL based on GaAs with InGa(Al)As superlattice active region. *Laser Physics Letters*, **2022**, 19, 075801	1.5	2
65	InAs quantum dots grown by MOCVD in GaAs and metamorphic InGaAs matrixes. *Journal of Physics: Conference Series*, **2017**, 816, 012024	0.3	1
64	Silicon Nanopillar Microarrays: Formation and Resonance Reflection of Light. *Semiconductors*, **2019**, 53, 205-209	0.7	1
63	Lasing of Injection Microdisks with InAs/InGaAs/GaAs Quantum Dots Transferred to Silicon. *Technical Physics Letters*, **2020**, 46, 783-786	0.7	1
62	Evaluation of the Impact of Surface Recombination in Microdisk Lasers by Means of High-Frequency Modulation. *Semiconductors*, **2019**, 53, 1099-1103	0.7	1
61	Optical properties of GaN x As y P1⊠⊡ semiconductor quaternary solid solutions. *Journal of Surface Investigation*, **2012**, 6, 479-481	0.5	1
60	Spectral dependence of the linewidth enhancement factor in quantum dot lasers. *Semiconductors*, **2013**, 47, 1656-1660	0.7	1
59	Investigation of the effect of surface passivation on microdisk lasers based on InGaAsN/GaAs quantum well active region. *Journal of Physics: Conference Series*, **2017**, 917, 052002	0.3	1
58	Epitaxial growth and investigation of GaP/GaP(As)N heterostructures on Si (100) 40 substrates. *Journal of Physics: Conference Series*, **2017**, 917, 032044	0.3	1
57	Investigation of whispering gallery modes in microlasers by scanning near-field optical microscopy. *Journal of Physics: Conference Series*, **2017**, 917, 052036	0.3	1
56	The effect of the sulfide passivation on the luminescence of microdisk mesas with quantum wells and quantum dots. *Journal of Physics: Conference Series*, **2015**, 643, 012043	0.3	1
55	Room temperature continuous wave operation of injection quantum dot microdisk lasers. *Journal of Physics: Conference Series*, **2015**, 643, 012002	0.3	1
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53	Optical properties of strain-compensated InAs/InGaAsN/GaAsN superlattices. *Technical Physics Letters*, **2007**, 33, 384-387	0.7	1
52	Structural and optical properties of heterostructures with InAs quantum dots in an InGaAsN quantum well grown by molecular-beam epitaxy. *Semiconductors*, **2004**, 38, 340-343	0.7	1
51	The effect of exposure to arsenic flow on the optical properties of quantum dot arrays in the InAs/GaAs(100) system. *Technical Physics Letters*, **2004**, 30, 272-274	0.7	1
50	Theoretical and experimental study of the effect of InAs growth rate on the properties of QD arrays in InAs/GaAs system. *Semiconductors*, **2003**, 37, 855-860	0.7	1

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43	Room temperature lasing in injection microdisks with InGaAsN/GaAs quantum well active region. *Journal of Physics: Conference Series*, **2018**, 1124, 081048	0.3	1
42	Edge-emitting and microdisk lasers based on hybrid quantum-well-dot structures **2018**,		1
41	Microdisk lasers based on GaInNAsSb/GaAsN quantum well active region. *Journal of Physics: Conference Series*, **2015**, 643, 012040	0.3	0
40	On-chip light detection using integrated microdisk laser and photodetector bonded onto Si board. *Laser Physics Letters*, **2022**, 19, 016201	1.5	0
39	A Micro Optocoupler Based on a Microdisk Laser and a Photodetector with an Active Region Based on Quantum Well-Dots. *Technical Physics Letters*, **2020**, 46, 629-632	0.7	0
38	Output power of multilayered InGaAs/GaAs quantum well-dot microdisk lasers. *Journal of Physics: Conference Series*, **2021**, 2086, 012081	0.3	0
37	Saturation Power of a Semiconductor Optical Amplifier Based on Self-Organized Quantum Dots. *Semiconductors*, **2021**, 55, S67-S71	0.7	0
36	Molecular-Beam Epitaxy Growth and Properties of AlGaAs Nanowires with InGaAs Nanostructures. *Physica Status Solidi - Rapid Research Letters*,2200056	2.5	0
35	Light absorption by an atomic force microscope probe. *Journal of Physics: Conference Series*, **2017**, 816, 012036	0.3	
34	Investigation of lasers based on coupled waveguides by near-field scanning optical microscopy. *Journal of Physics: Conference Series*, **2017**, 929, 012070	0.3	
33	Electrically pumped microdisk lasers with semitransparent conducting pyrolytic carbon film. *Journal of Physics: Conference Series*, **2016**, 741, 012076	0.3	
32	Optimization of the design and mode of operation of a QD laser for reducing the heat-to-bitrate ratio. *Semiconductors*, **2013**, 47, 1097-1102	0.7	

31	Near-field mapping of three-particle plasmonic structures. *Journal of Physics: Conference Series*, **2017**, 917, 062012	0.3
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29	Metamorphic InAs quantum dots: Photoluminescence features related to cooperative phenomena in the quantum dot-matrix system. *Technical Physics Letters*, **2007**, 33, 590-593	0.7
28	Engineering of the radiative recombination rate in quantum dots coupled to the tilted cavity waveguide mode. *Semiconductor Science and Technology*, **2006**, 21, 162-166	1.8
27	Comparative study of GaAs-based 1.5 micron-range InAs/InGaAs and InAs/InAlAs self-assembled quantum dots. *Physica Status Solidi (A) Applications and Materials Science*, **2006**, 203, 1359-1364	1.6
26	Optical study of resonant states in GaN x As1 . *Semiconductors*, **2006**, 40, 1162-1164	0.7
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20	Investigation of microdisk and microring lasers based on InGaAs/GaAs QWDs by the interferometry method. *Journal of Physics: Conference Series*, **2020**, 1695, 012093	0.3
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